AMENDMENTS TO THE CLAIMS:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Cancelled)

2. (Currently Amended) A portable telephone comprising:

a display device, the display device comprising:

a substrate; and

a plurality of pixels over the substrate, each of the plurality of pixels comprising:

a first thin film transistor;

a second thin film transistor comprising a gate electrode electrically connected to the first thin film transistor; and

an electroluminescence element electrically connected to the second thin film transistor,

wherein the first thin film transistor comprises at least two channel regions in an active layer, [[and]] at least two gate electrodes corresponding to the channel regions, over the active layer with a gate insulating film interposed therebetween, and an impurity region interposed between the channel regions.

3. (Currently Amended) A portable telephone according to claim 2, wherein each of the first and second thin film transistors has at least one lightly doped impurity region between a channel region and at least one of a drain or the impurity region, the lightly doped impurity region of the first thin film transistor does not overlap a gate electrode of the first thin film transistor and the lightly doped impurity region of the second thin film transistor overlaps [[a]] the gate electrode of the second thin film transistor at least partly.

4. (Previously Presented) A portable telephone according to claim 2, wherein the first thin film transistor is a switching thin film transistor and the second thin film transistor is a current control thin film transistor.

5. (Currently Amended) A portable telephone comprising:

a display device, the display device comprising:

a substrate; and

a plurality of pixels over the substrate, each of the plurality of pixels comprising:

a first thin film transistor;

a second thin film transistor comprising a gate electrode electrically connected to the first thin film transistor; and

an electroluminescence element electrically connected to the second thin film transistor,

wherein the first thin film transistor comprises at least two channel regions in an active layer, [[and]] at least two gate electrodes corresponding to the channel regions, over the active layer with a gate insulating film interposed therebetween, and an impurity region interposed between the channel regions, and

wherein a channel width of the second thin film transistor is greater than a channel width of the first thin film transistor.

6. (Currently Amended) A portable telephone according to claim 5, wherein each of the first and second thin film ~~transistor~~ transistors has at least one lightly doped impurity region between a channel region and at least one of a drain or the impurity region, the lightly doped impurity region of the first thin film transistor does not overlap a gate electrode of the first thin film transistor and the lightly doped impurity region of the second thin film transistor overlaps [[a]] the gate electrode of the second thin film transistor at least partly.

7. (Previously Presented) A portable telephone according to claim 5, wherein the first thin film transistor is a switching thin film transistor and the second thin film transistor is a current control thin film transistor.

8. (Previously Presented) A portable telephone comprising:

a display device, the display device comprising:

a substrate; and

a plurality of pixels over the substrate, each of the plurality of pixels comprising:

a first thin film transistor;

a second thin film transistor comprising a gate electrode electrically connected to the first thin film transistor; and

an electroluminescence element electrically connected to the second thin film transistor,

wherein at least the first thin film transistor comprises an active layer in which two or more channel regions connected in series are formed, and

wherein an equation of $W2/L2 \geq 5 \times W1/L1$ is established where a channel length of the second thin film transistor is L2, a channel width of the second thin film transistor is W2, a channel length of the first thin film transistor is L1 and a channel width of the first thin film transistor is W1.

9. (Currently Amended) A portable telephone according to claim 8, wherein each of the first and second thin film ~~transistor~~ transistors has at least one lightly doped impurity region, the lightly doped impurity region of the first thin film transistor does not overlap a gate electrode of the first thin film transistor, and the lightly doped impurity region of the second thin film transistor overlaps [[a]] the gate electrode of the second thin film transistor at least partly.

10. (Previously Presented) A portable telephone according to claim 8, wherein the first thin film transistor is a switching thin film transistor and the second thin film transistor is a current control thin film transistor.

11. (Previously Presented) A portable telephone according to claim 8, wherein the channel length of the second thin film transistor (L2) is 0.1 to 50 μm, the channel width of the second thin film transistor (W2) is 0.5 to 30 μm, the channel length of the first thin film transistor (L1) is 0.2 to 18 μm and the channel width of the first thin film transistor (W1) is 0.1 to 5 μm.

12. (Withdrawn) A portable telephone comprising:

a display device, the display device comprising:

a substrate; and

a plurality of pixels over the substrate, each of the plurality of pixels comprising:

a first thin film transistor;

a second thin film transistor comprising a gate electrode electrically connected to the first thin film transistor; and

an electroluminescence element electrically connected to the second thin film transistor,

wherein the first thin film transistor comprises at least two gate electrodes over the substrate, at least two channel regions corresponding to the gate electrode, over the gate electrode with a gate insulating film interposed therebetween, and an impurity region interposed between the channel regions, and

wherein the impurity region has the same impurity concentration as a source or drain regions of the first thin film transistor.

13. (Withdrawn) A portable telephone according to claim 12, wherein the first thin film transistor is a switching thin film transistor and the second thin film transistor is a current control thin film transistor.

14. (Withdrawn) A portable telephone according to claim 12, wherein an equation of $W2/L2 \geq 5 \times W1/L1$ is established where a channel length of the second thin film transistor is L2, a channel width of the second thin film transistor is W2, a channel length of the first thin film transistor is L1 and a channel width of the first thin film transistor is W1.

15. (Withdrawn-Currently Amended) A portable telephone according to claim 12, wherein [[the]] a channel length of the second thin film transistor (L2) is 0.1 to 50 μm, [[the]] a channel width of the second thin film transistor (W2) is 0.5 to 30 μm, [[the]] a channel length of the first thin film transistor (L1) is 0.2 to 18 μm and the channel width of the first thin film transistor (W1) is 0.1 to 5 μm.

16. (Withdrawn) A portable telephone according to claim 12, wherein the substrate comprises a material selected from the group consisting of a glass, a glass ceramic, a quartz, a silicon, a ceramic, a metal, and a plastic.

17. (Withdrawn) A portable telephone comprising:

a display device, the display device comprising:

a substrate; and

a plurality of pixels over the substrate, each of the plurality of pixels comprising:

a first thin film transistor;

a second thin film transistor comprising a gate electrode electrically connected to the first thin film transistor; and

an electroluminescence element electrically connected to the second

thin film transistor,

wherein the first thin film transistor comprises at least two gate electrodes over the substrate, at least two channel regions corresponding to the gate electrode, over the gate electrode with a gate insulating film interposed therebetween, and an impurity region interposed between the channel regions,

wherein a channel width of the second thin film transistor is greater than a channel width of the first thin film transistor, and

wherein the impurity region has the same impurity concentration as a source or drain regions of the first thin film transistor.

18. (Withdrawn) A portable telephone according to claim 17, wherein the first thin film transistor is a switching thin film transistor and the second thin film transistor is a current control thin film transistor.

19. (Withdrawn) A portable telephone according to claim 17, wherein the substrate comprises a material selected from the group consisting of a glass, a glass ceramic, a quartz, a silicon, a ceramic, a metal, and a plastic.

20. (Currently Amended) A portable telephone comprising:

a display device, the display device comprising:

a substrate; and

a plurality of pixels over the substrate, each of the plurality of pixels comprising:

a first thin film transistor;

a second thin film transistor comprising a gate electrode electrically connected to the first thin film transistor; and

an electroluminescence element electrically connected to the second thin film transistor,

wherein the first thin film transistor comprises an active layer in which

at least two channel regions connected in series are formed with an impurity region interposed therebetween, and

wherein each of the first and second thin film transistors has at least one lightly doped impurity region between a channel region and at least one of a drain region or [[an]] the impurity region, the lightly doped impurity region of the first thin film transistor does not overlap a gate electrode of the first thin film transistor and the lightly doped impurity region of the second thin film transistor overlaps [[a]] the gate electrode of the second thin film transistor at least partly.

21. (Currently Amended) A portable telephone according to claim 20, wherein the first thin film transistor is a switching thin film transistor and the second thin film transistor is a current control thin film transistor.

22. (Previously Presented) A portable telephone according to claim 20, wherein the substrate comprises a material selected from the group consisting of a glass, a glass ceramic, a quartz, a silicon, a ceramic, a metal, and a plastic.

23. (Previously Presented) A portable telephone comprising:

a display device, the display device comprising:

a substrate; and

a plurality of pixels over the substrate, each of the plurality of pixels comprising:

a switching element comprising an active layer and at least first and second gate electrodes adjacent to the active layer with a gate insulating film interposed therebetween;

a current control element comprising a gate electrode electrically connected to the switching element; and

an electroluminescence element electrically connected to the current control element.

24. (Previously Presented) A portable telephone according to claim 23, wherein the substrate comprises a material selected from the group consisting of a glass, a glass ceramic, a quartz, a silicon, a ceramic, a metal, and a plastic.

25. (Previously Presented) A portable telephone comprising:

a display device, the display device comprising:

a substrate; and

a plurality of pixels over the substrate, each of the plurality of pixels comprising:

a switching element comprising an active layer and at least first and second gate electrodes adjacent to the active layer with a gate insulating film interposed therebetween;

a current control element comprising a gate electrode electrically connected to the switching element; and

an electroluminescence element electrically connected to the current control element,

wherein a channel width of the current control element is greater than a channel width of the switching element.

26. (Previously Presented) A portable telephone according to claim 25, wherein the substrate comprises a material selected from the group consisting of a glass, a glass ceramic, a quartz, a silicon, a ceramic, a metal, and a plastic.

27. (Currently Amended) A portable telephone comprising:

a display device, the display device comprising:

a substrate; and

a plurality of pixels over the substrate, each of the plurality of pixels comprising:

a switching element comprising an active layer and at least first and second gate electrodes adjacent to [[an]] the active layer with a gate insulating film interposed therebetween;

a current control element comprising a gate electrode electrically connected to the switching element; and

an electroluminescence element electrically connected to the current control element,

wherein each of the switching element and the current control element has at least one lightly doped impurity region between a channel region and at least one of a drain region or an impurity region, the lightly doped impurity region of the switching element does not overlap a gate electrode of the switching element and the lightly doped impurity region of the current control element overlaps [[a]] the gate electrode of the current control element at least partly.

28. (Previously Presented) A portable telephone according to claim 27, wherein the substrate comprises a material selected from the group consisting of a glass, a glass ceramic, a quartz, a silicon, a ceramic, a metal, and a plastic.

29. (Previously Presented) A portable telephone comprising:

a display device, the display device comprising:

a substrate; and

a plurality of pixels over the substrate, each of the plurality of pixels comprising:

a switching element comprising at least two thin film transistors;

a current control element comprising a gate electrode electrically connected to the switching element; and

an electroluminescence element electrically connected to the current control element.

30. (Previously Presented) A portable telephone according to claim 29, wherein the

substrate comprises a material selected from the group consisting of a glass, a glass ceramic, a quartz, a silicon, a ceramic, a metal, and a plastic.

31. (Previously Presented) A portable telephone comprising:

a display device, the display device comprising:

a substrate; and

a plurality of pixels over the substrate, each of the plurality of pixels comprising:

a switching element comprising at least two thin film transistors;

a current control element comprising a gate electrode electrically connected to the switching element; and

an electroluminescence element electrically connected to the current control element,

wherein a channel width of the current control element is greater than a channel width of the switching element.

32. (Previously Presented) A portable telephone according to claim 31, wherein the substrate comprises a material selected from the group consisting of a glass, a glass ceramic, a quartz, a silicon, a ceramic, a metal, and a plastic.

33. (Withdrawn-Currently Amended) A portable telephone comprising:

a display device, the display device comprising:

a substrate; and

a plurality of pixels over the substrate, each of the plurality of pixels comprising:

a switching element comprising at least two thin film transistors;

a current control element comprising a gate electrode electrically

connected to the switching element; and

an electroluminescence element electrically connected to the current control element,

wherein each of the switching element and the current control element has at least one lightly doped impurity region between a channel region and at least one of a drain region or an impurity region, the lightly doped impurity region of the switching element does not overlap a gate electrode of the switching element and the lightly doped impurity region of the current control element overlaps [[a]] the gate electrode of the current control element at least partly.

34. (Withdrawn) A portable telephone according to claim 33, wherein the substrate comprises a material selected from the group consisting of a glass, a glass ceramic, a quartz, a silicon, a ceramic, a metal, and a plastic.

35. (New) A portable telephone according to claim 2, wherein a top surface of the impurity region is entirely in contact with the gate insulating film.

36. (New) A portable telephone according to claim 5, wherein a top surface of the impurity region is entirely in contact with the gate insulating film.

37. (New) A portable telephone according to claim 8, wherein, in a region between the channel regions, a top surface of the active layer is entirely in contact with a gate insulating film.

38. (New) A portable telephone according to claim 20, wherein, in a region between the channel regions, a top surface of the active layer is entirely in contact with a gate insulating film.

39. (New) A portable telephone according to claim 23, wherein, in a region between the first gate electrode and the second gate electrode, a top surface of the active layer is entirely in

contact with the gate insulating film.

40. (New) A portable telephone according to claim 25, wherein, in a region between the first gate electrode and the second gate electrode, a top surface of the active layer is entirely in contact with the gate insulating film.

41. (New) A portable telephone according to claim 27, wherein, in a region between the first gate electrode and the second gate electrode, a top surface of the active layer is entirely in contact with the gate insulating film.

42. (New) A portable telephone according to claim 29,wherein each of the thin film transistors of the switching element comprises an active layer and a gate electrode with an gate insulating film therebetween, and wherein, in a region between the gate electrodes of the thin film transistors of the switching element, a top surface of the active layer is entirely in contact with the gate insulating film.

43. (New) A portable telephone according to claim 31, wherein each of the thin film transistors of the switching element comprises an active layer and a gate electrode with an gate insulating film therebetween, and wherein, in a region between the gate electrodes of the thin film transistors of the switching element, a top surface of the active layer is entirely in contact with the gate insulating film.